



140V PNP MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features

- BV_{CEO} > -140V
- BV_{CBO} > -140V
- I_C = -500m Continuous Current
- hFE > 250 for High Gain @ -0.2A
- Very Low VCEsat
- Complementary NPN Type: FZT694B
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

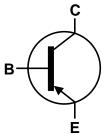
Applications

Battery Powered Circuits

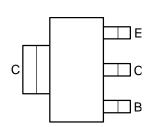




Top View



Device Symbol



Top View Pin-Out

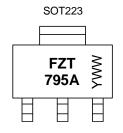
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT795ATA	AEC-Q101	FZT795A	7	12	1,000
FZT795AQTA	Automotive	FZT795A	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- $5.\ For\ packaging\ details,\ go\ to\ our\ website\ at\ http://www.diodes.com/products/packages.html.$

Marking Information



FZT 795A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-140	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-140	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-500	mA
Peak Pulse Current	I _{CM}	-1	Α

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	0	2	W
Power Dissipation	(Note 7)	P _D	3	W
Thermal Resistance, Junction to Ambient	(Note 6)	D	62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	12.9	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

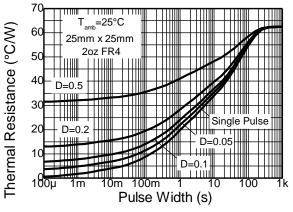
Notes:

- 6. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 7. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

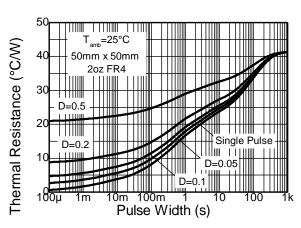




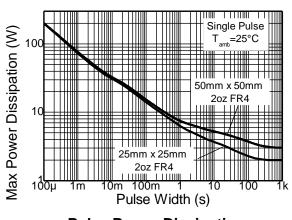
Thermal Characteristics and Derating Information



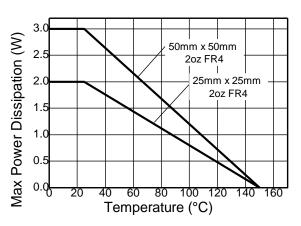
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



Derating Curve



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

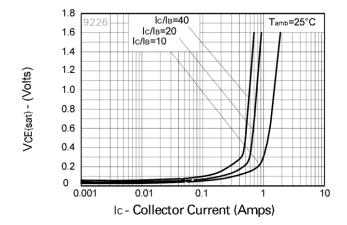
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-140	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-140	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	I _E = -100μA
Collector-Base Cut-Off Current	I _{CBO}	_	_	-100	nA	V _{CB} = -100V
Collector-Emitter Cut-Off Current	I _{CES}	_	_	-100	nA	V _{CE} = -100V
Emitter Cut-Off Current	I _{EBO}	_	_	-100	nA	V _{EB} = -6V
DC Current Gain (Note 10)	h _{FE}	300 250 100	_ _ _	800 — —	_	I _C = -10mA, V _{CE} = -2V I _C = -200mA, V _{CE} = -2V I _C = -300mA, V _{CE} = -2V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	_ _ _	_ _ _	-300 -300 -250	mV	$I_C = -100$ mA, $I_B = -1$ mA $I_C = -200$ mA, $I_B = -5$ mA $I_C = -500$ mA, $I_B = -50$ mA
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	_	_	-0.95	V	I _C = -500mA, I _B = -50mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	_	-0.75	_	V	I _C = -500mA, V _{CE} = -2V
Input Capacitance	C _{ibo}	_	225	_	pF	V _{EB} = -0.5V, f = 1MHz
Output Capacitance	C _{obo}	_	15	_	pF	V _{CB} = -10V, f = 1MHz
Current Gain-Bandwidth Product	f _T	100	_	_	MHz	V _{CE} = -5V, I _C = -50mA, f=50MHz
Turn-On Time	t _{on}	_	100	_	ns	V _{CC} = -50V, I _C = -100mA
Turn-Off Time	t _{off}	_	1900	_	ns	$I_{B1} = -I_{B2} = 10mA$

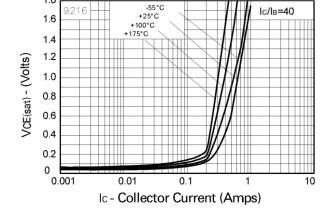
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.





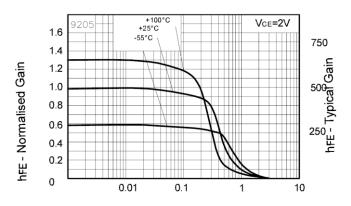
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



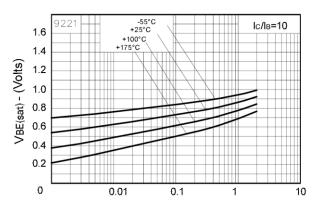


1.8

VCE(sat) v IC



VCE(sat) v IC

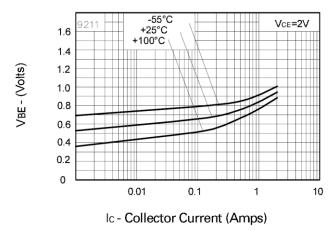


Ic - Collector Current (Amps)

Ic - Collector Current (Amps)

VBE(sat) v IC





0.1 0.01 0.01 0.00

VCE - Collector Emitter Voltage (V)

100

10

VBE(on) v IC

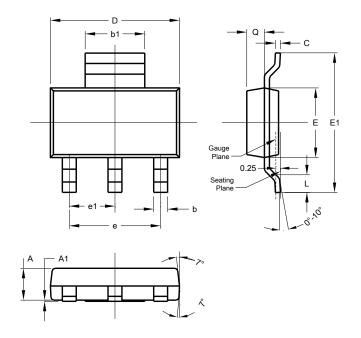
Safe Operating Area

1000



Package Outline Dimensions

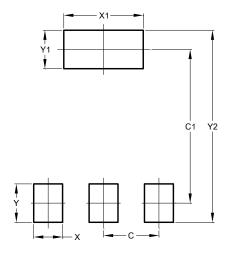
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Ø	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00





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